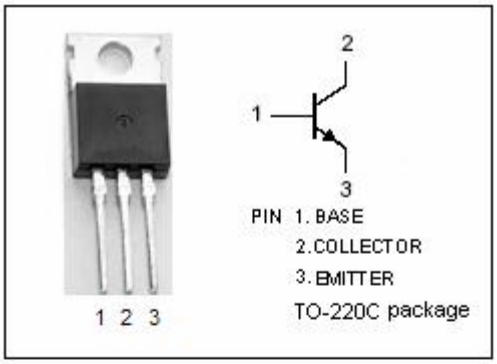
isc Silicon NPN Power Transistor KSD880



DESCRIPTION

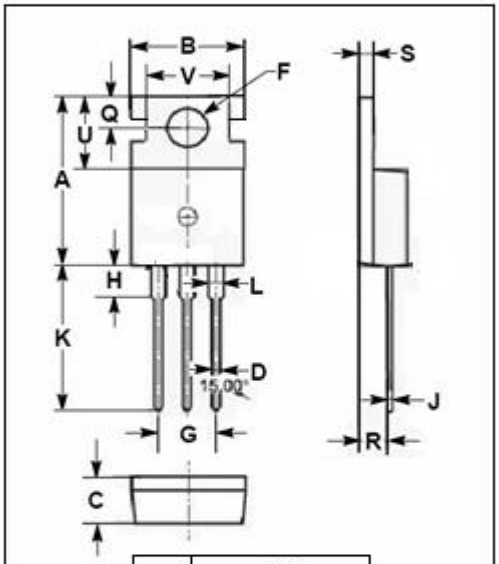
- Collector-Emitter sustaining Voltage
  : V_{CEO}=60V(Min)
- Good Linearity of h_{FE}
- Complement to KSB834
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Linear and switching industrial applications

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	3	A
I_B	Base Current- Continuous	0.3	A
P_C	Total Power Dissipation @ T_C=25℃	30	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

isc Silicon NPN Power Transistor KSD880

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(sus)}$	Collector-Emitter Breakdown Voltage	I_C=50mA ; I_B= 0	60			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 3A; I_B= 0.3A			1	V
$V_{BE(on)}$	Base-Emitter OnVoltage	I_C= 0.5A; V_{CE}= 5V			1	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 60V ; I_E= 0			100	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}=7V; I_C= 0			100	μA
h_{FE-1}	DC Current Gain	I_C=0.5A ; V_{CE}=5V	60		300	
h_{FE-2}	DC Current Gain	I_C=3A ; V_{CE}=5V	20			

◆ **h_{FE-1} Classifications**

O	Y	G
60-120	100-200	150-300